

SANYO	No.4243A	2SJ281
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

Absolute Maximum Ratings at Ta = 25°C

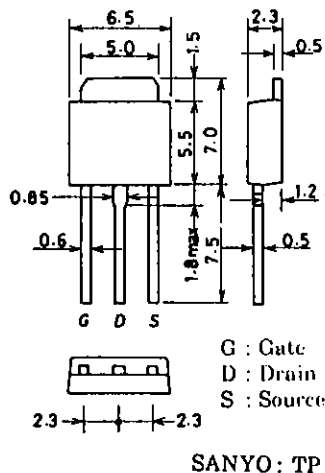
Drain to Source Voltage	V _{DS}	-250	V	unit
Gate to Source Voltage	V _{GS}	±30	V	
Drain Current(DC)	I _D	-3	A	
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%		-12 A
Allowable Power Dissipation	P _D	1.0	W	
		Tc = 25°C		30 W
Channel Temperature	T _{ch}	150	°C	
Storage Temperature	T _{stg}	-55 to +150		°C

Electrical Characteristics at Ta = 25°C

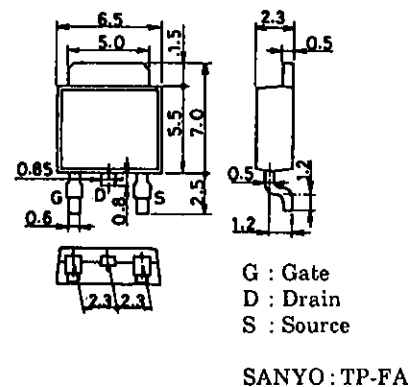
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-250			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -250V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±25V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.5		-2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -1.5A	1.5	2.5		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = -1.5A, V _{GS} = -10V		1.5	2.0	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		420		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		100		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		40		pF

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Package Dimensions 2083A
(unit : mm)



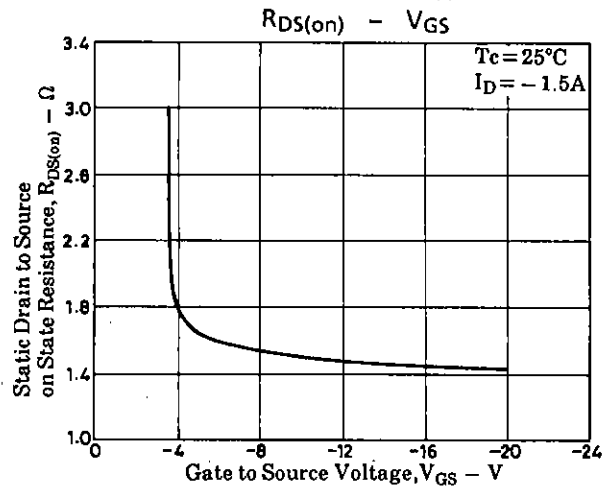
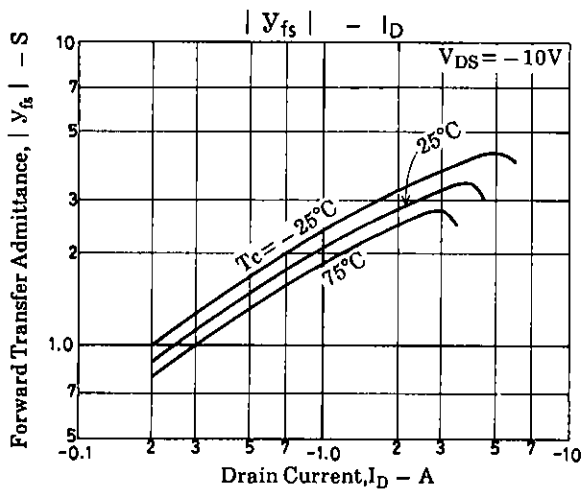
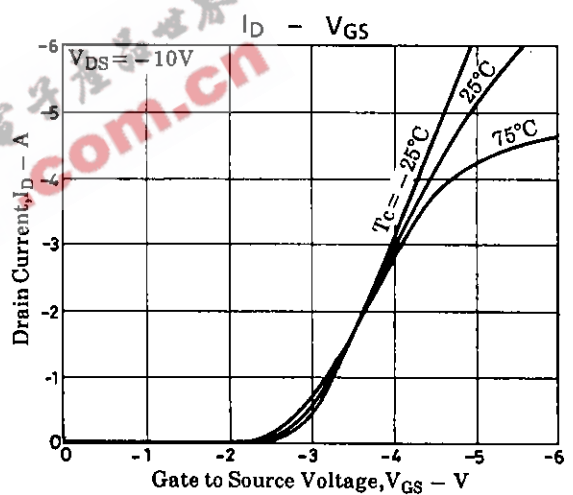
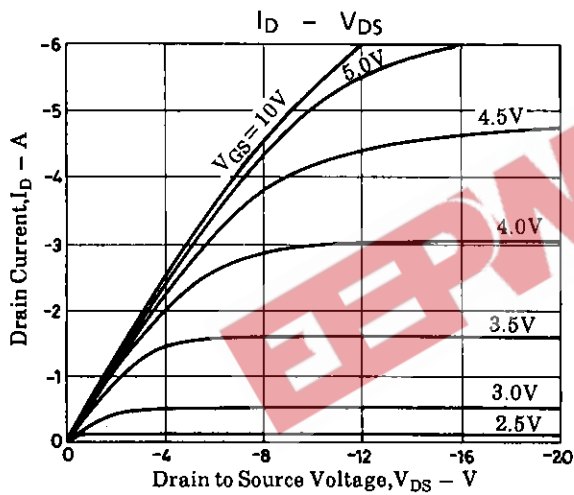
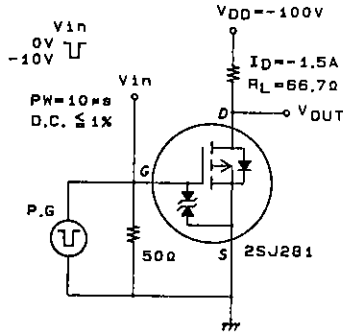
Package Dimensions 2092A
(unit : mm)

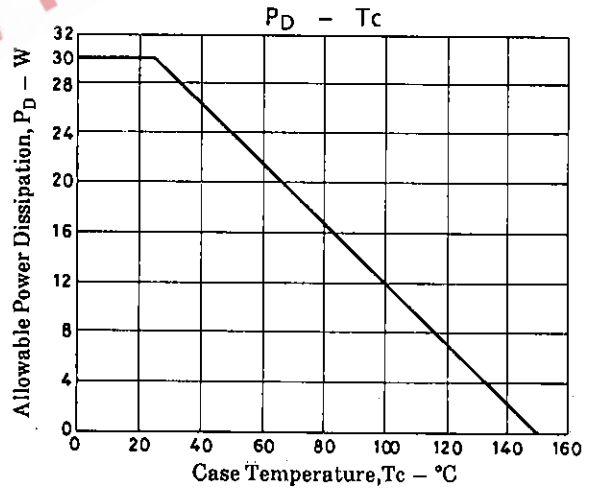
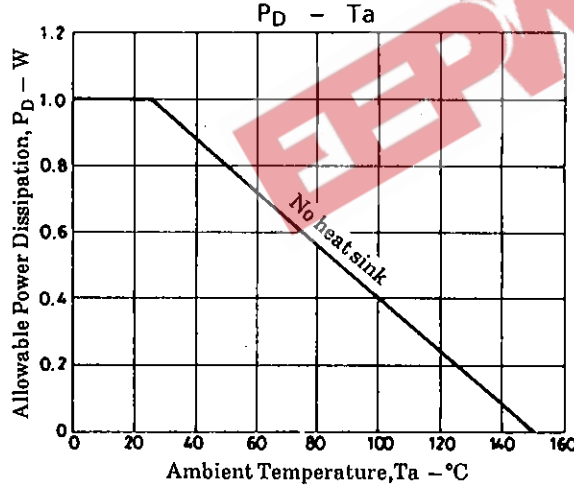
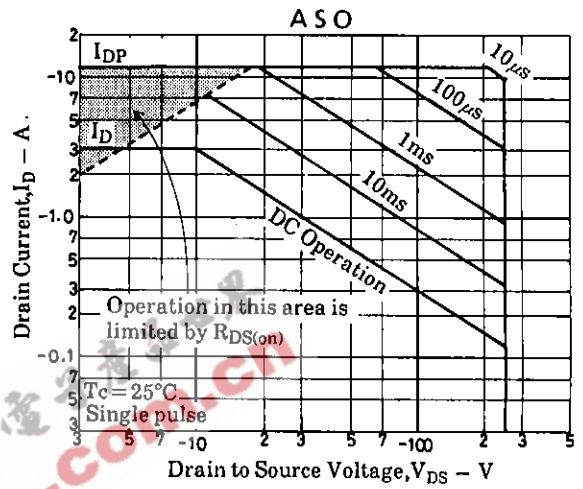
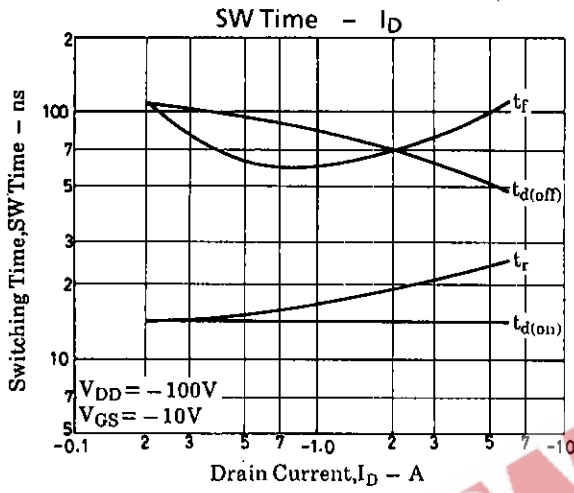
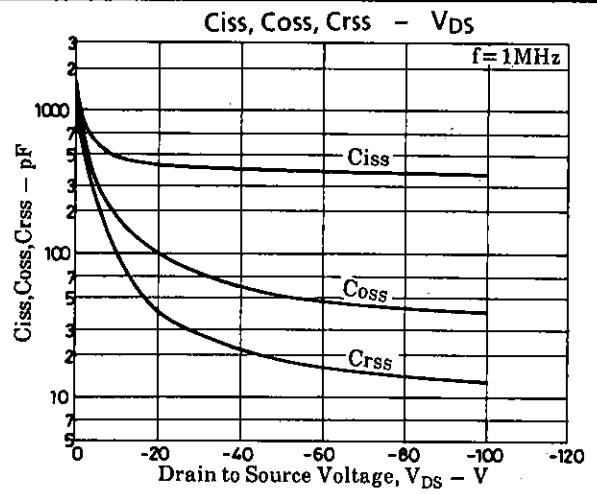
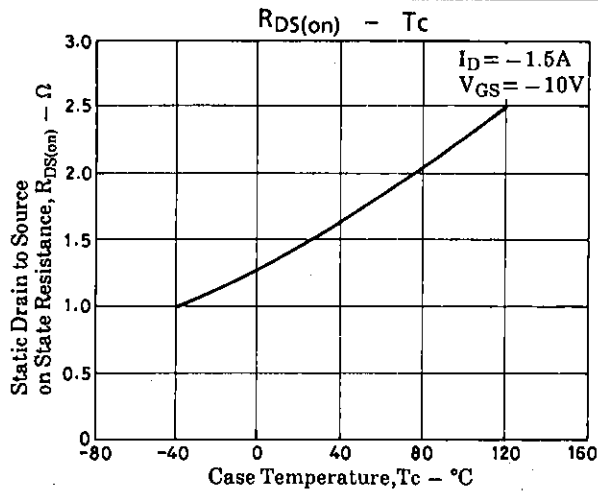


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			min	typ	max	unit
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		14		ns
Rise Time	t_r	"		18		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		75		ns
Fall Time	t_f	"		65		ns
Diode Forward Voltage	V_{SD}	$I_S = -3A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit





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